# 1. General description

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- · Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

# 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Limiting values	Limiting values FET1 and FET2							
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	80	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	21	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	64	W	
Static characte	eristics FET1 and FET2				•			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 11		-	12.5	16.7	mΩ	
Dynamic chara	acteristics FET1 and FE	T2			•			
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	10.4	-	nC	
Source-drain o	liode FET1 and FET2							
Q <sub>r</sub>	recovered charge	$I_S$ = 10 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; $T_j$ = 25 °C		-	37.1	-	nC	



# Dual N-channel 80 V, 17 $m\Omega$ standard level MOSFET

# 5. Pinning information

## **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4	
8	D1	drain1	LFPAK56D (SOT1205)	

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK7K17-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

# 7. Marking

# Table 4. Marking codes

Type number	Marking code
BUK7K17-80E	71780E

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# Dual N-channel 80 V, 17 mΩ standard level MOSFET

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Limiting val	ues FET1 and FET2			_		
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
$V_{DGR}$	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	64	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	21	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	15	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	84	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drai	n diode FET1 and FET2				'	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	21	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	84	Α
Avalanche r	uggedness FET1 and FET2			'	_	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 21 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1] [2]	-	116	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$  Refer to application note AN10273 for further information.

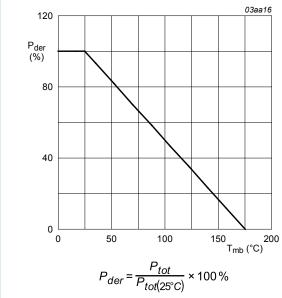


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

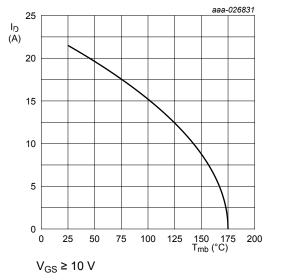
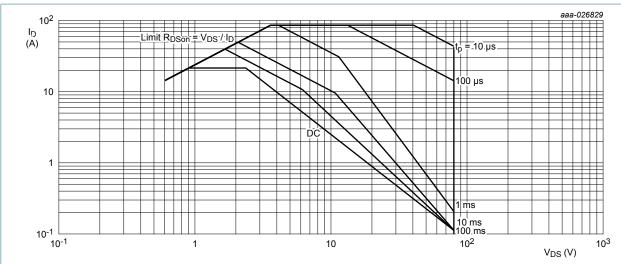


Fig. 2. Continuous drain current as a function of mounting base temperature, FET1 and FET2

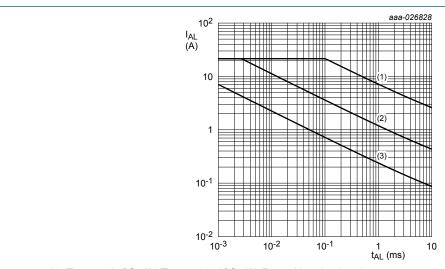
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## Dual N-channel 80 V, 17 mΩ standard level MOSFET



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2



(1)  $T_{i \text{ (init)}} = 25^{\circ}\text{C}$ ; (2)  $T_{i \text{ (init)}} = 150^{\circ}\text{C}$ ; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

## Dual N-channel 80 V, 17 $m\Omega$ standard level MOSFET

# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.36	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

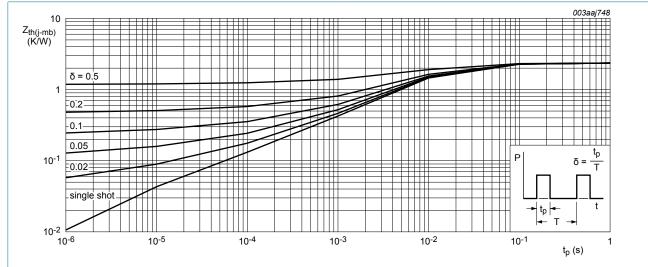


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2

# Dual N-channel 80 V, 17 m $\Omega$ standard level MOSFET

# 10. Characteristics

#### Table 7. Characteristics

Symbol Pa	arameter	Conditions	Min	Тур	Max	Unit
Static characteris	stics FET1 and FET2					
(DI ()DOO	rain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	80	-	-	V
br	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	72	-	-	V
()	ate-source threshold oltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	1	-	-	V
I <sub>DSS</sub> dr	rain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub> ga	ate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
DOON	rain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 11	-	12.5	16.7	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 175 °C; Fig. 12	-	-	42	mΩ
Dynamic characte	eristics FET1 and FE	T2		1		
Q <sub>G(tot)</sub> to	tal gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V;	-	32.4	-	nC
Q <sub>GS</sub> ga	ate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	7.1	-	nC
Q <sub>GD</sub> ga	ate-drain charge		-	10.4	-	nC
C <sub>iss</sub> in	put capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1701	2262	pF
C <sub>oss</sub> ou	utput capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	174	208	pF
100	everse transfer apacitance		-	104	142	pF
t <sub>d(on)</sub> tu	rn-on delay time	$V_{DS} = 60 \text{ V}; R_L = 5 \Omega; V_{GS} = 10 \text{ V};$	-	8.1	-	ns
t <sub>r</sub> ris	se time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	11.1	-	ns
t <sub>d(off)</sub> tu	rn-off delay time		-	22.5	-	ns
t <sub>f</sub> fa	II time		-	13.4	-	ns
Source-drain dio	de FET1 and FET2		'	'		•
V <sub>SD</sub> so	ource-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t <sub>rr</sub> re	verse recovery time	$I_S = 10 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{GS} = 0 \text{ V;}$	_	30.1	-	ns
rr   ic		V <sub>DS</sub> = 25 V; T <sub>i</sub> = 25 °C				

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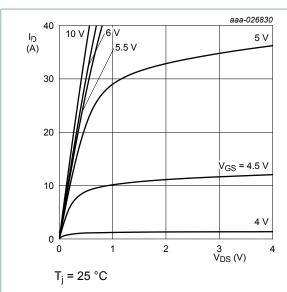


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

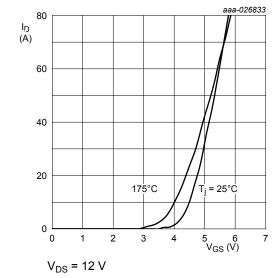


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, FET1 and FET2

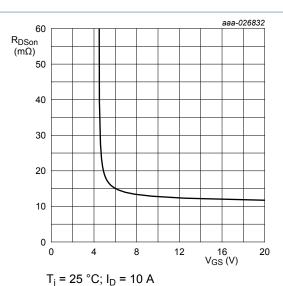
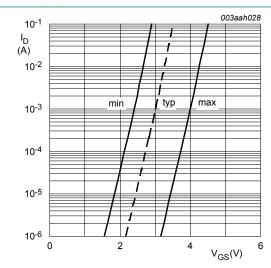


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$ 

Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2

## Dual N-channel 80 V, 17 mΩ standard level MOSFET

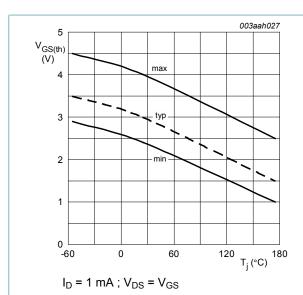


Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2

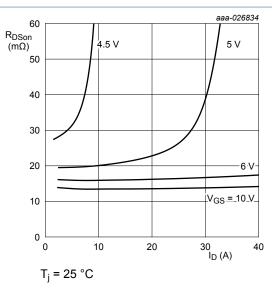


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values, FET1 and FET2

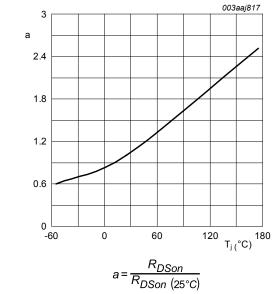


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2

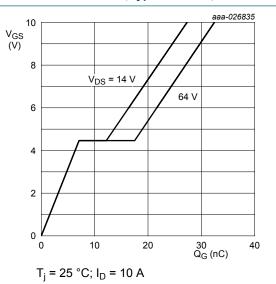


Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

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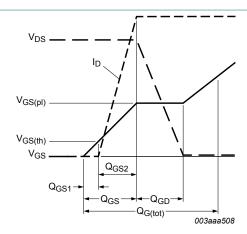
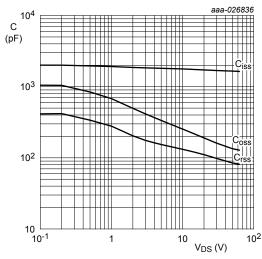
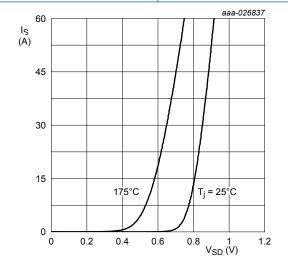


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2

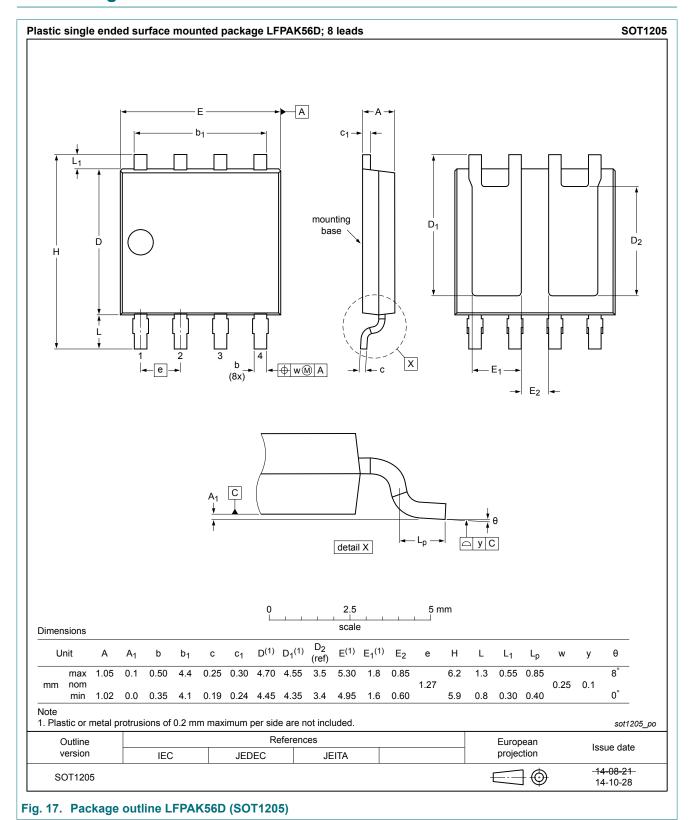


 $V_{GS} = 0 V$ 

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

### Dual N-channel 80 V, 17 mΩ standard level MOSFET

# 11. Package outline



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# 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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